

14th RD50 Workshop

Wednesday 3 June 2009

Pad Detector Characterization and Defect Engineering (13:50 - 18:40)

time	[id] title	presenter
13:50	[14] Capacitance Measurements and Depletion Voltage for Annealed Fz and MCz Diodes	METCALFE, Jessica
14:10	[28] Determination of depletion voltage from CV, IV and CCE measurements on Pad Detectors	KASKA, Katharina
14:30	[16] Electrical Characterization of Irradiated Silicon Diodes at Different Temperature	KHOMENKOV, Vladimir
14:50	[15] TCT-Measurements of mixed irradiated Magentic Czochralski Diodes in the SLHC-Scenario	EBER, Robert
15:10	[24] Charge collection and trapping effects in n-type and p-type epitaxial silicon diodes after proton irradiation	LANGE, Joern
15:30	Coffee break	
16:00	[5] Determination of strip detector properties by using Edge-TCT	KRAMBERGER, Gregor
16:20	[29] New TCT setups at CERN and Louvain	FAHRER, Manuel
16:40	[11] Predictions on charge collection efficiency in heavily irradiated Si detectors basing on the approach of active base region	VERBITSKAYA, Elena
17:00	[2] Contributions of Electrons and Holes to Total Collected Charge in Heavily Irradiated Si Pad and Strip/Pixel Detectors: A Comparison Simulation Study	LI, Zheng
17:20	[39] Bias on-off proton irradiation results on MCz-Si and Fz-si detectors	HAERKOENEN, Jasu
17:40	[9] Sensor R&D for an upgrade of the CMS pixel barrel	SIBILLE, Jennifer Ann SIBILLE, Jennifer Ann
18:00	[30] Discussion Session	FRETWURST, Eckhart KRAMBERGER, Gregor